Philips Semiconductors

Product specification

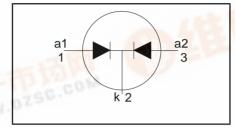
Rectifier diodes Schottky barrier

PBYR325CTD series

FEATURES

- Low forward volt drop
- Fast switching
- Reverse surge capability
- High thermal cycling performance
- · Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

$$V_R = 20 \text{ V/ } 25 \text{ V}$$

$$I_{O(AV)} = 3 \text{ A}$$

$$V_F \le 0.4 \text{ V}$$

GENERAL DESCRIPTION

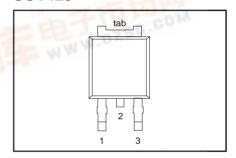
Dual schottky rectifier diodes intended for use as output rectifiers in low voltage, high frequency switched mode power supplies.

The PBYR325CTD series is supplied in the SOT428 surface mounting package.

PINNING

PIN	DESCRIPTION		
1	anode 1		
2	cathode ¹		
3	anode 2		
tab	cathode		

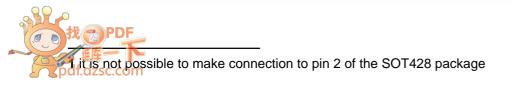
SOT428



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	I. MAX.		UNIT
V_{RRM}	Peak repetitive reverse	PBYR3	4.	20CTD 20	25CTD 25	V
V_{RWM}	voltage Working peak reverse voltage	场网	-	20	25	V
V_R	Continuous reverse voltage	T _{mb} ≤ 125 °C	-	20	25	V
I _{O(AV)}	Average rectified output current (both diodes conducting)	square wave; δ = 0.5; $T_{mb} \le 144$ °C	-	;	3	А
I _{FRM}	Repetitive peak forward current per diode	square wave; $\delta = 0.5$; $T_{mb} \le 144$ °C	-	- =	3	Α
I _{FSM}	Non-repetitive peak forward current per diode	t = 10 ms t = 8.3 ms sinusoidal; $T_j = 125 ^{\circ}\text{C}$ prior to surge; with reapplied $V_{\text{RRM(max)}}$	F	5 1 W W 16	5 0	A A
I _{RRM}	Peak repetitive reverse surge current per diode	pulse width and repetition rate limited by T _{i max}	-		1	Α
T _j	Operating junction temperature	a.G.COM	-	15	50	°C
T_{stg}	Storage temperature		- 65	17	75	°C



Rectifier diodes Schottky barrier PBYR325CTD series

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
R _{th j-a}	to mounting base	per diode both diodes pcb mounted, minimum footprint, FR4 board	- - -	- - 50	5 4 -	K/W K/W K/W

ELECTRICAL CHARACTERISTICS

All characteristics are per diode at $T_i = 25$ °C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{F}	Forward voltage	$I_{\rm F} = 1.5 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.34	0.4	V
·		$I_{\rm F} = 3 \text{ A}; T_{\rm i} = 125^{\circ}\text{C}$	-	0.39	0.5	V
		$I_{\rm F} = 3 \text{A}$	-	0.47	0.6	V
I_R	Reverse current	$\dot{V}_{R} = V_{RWM}$	-	0.05	2	mΑ
		$V_{R} = V_{RWM}$; $T_{i} = 100^{\circ}C$	-	4	8	mΑ
C_d	Junction capacitance	$V_R = 5 \text{ V}$; $f = 1 \text{ MHz}$, $T_i = 25 \text{ °C to } 125 \text{ °C}$	-	117	-	pF

Rectifier diodes Schottky barrier

PBYR325CTD series

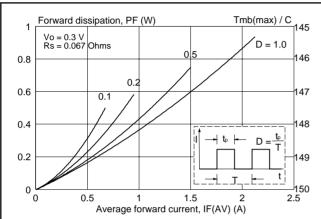


Fig.1. Maximum forward dissipation per diode $P_F = f(I_{F(AV)})$; square current waveform where $I_{F(AV)} = I_{F(RMS)} x \sqrt{D}$.

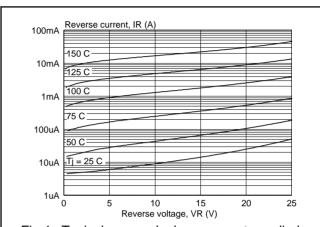


Fig.4. Typical reverse leakage current per diode; $I_R = f(V_R)$; parameter T_j

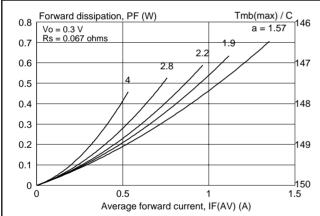


Fig.2. Maximum forward dissipation per diode $P_F = f(I_{F(AV)})$; sinusoidal current waveform where a = f(AV).

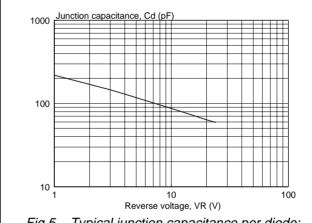


Fig.5. Typical junction capacitance per diode; $C_d = f(V_R)$; f = 1 MHz; $T_j = 25$ °C to 125 °C.

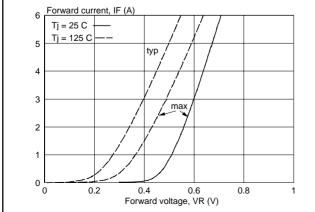


Fig.3. Typical and maximum forward characteristic per diode $I_F = f(V_F)$; parameter T_i

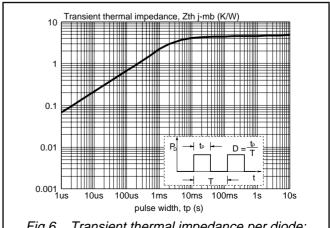
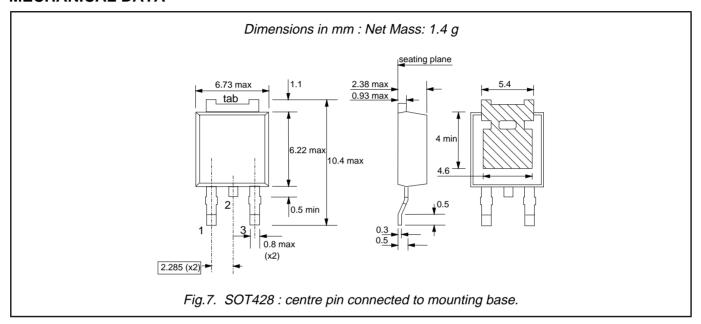


Fig.6. Transient thermal impedance per diode; $Z_{th j \cdot mb} = f(t_p)$.

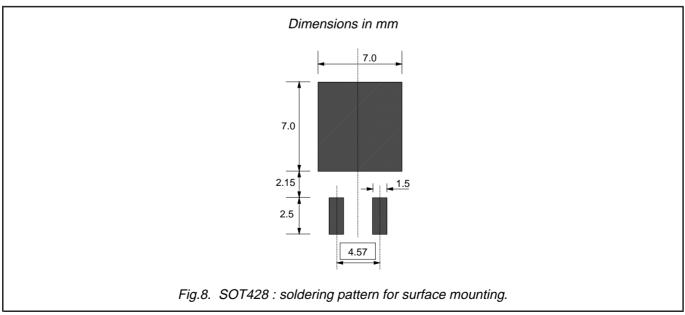
Philips Semiconductors Product specification

Rectifier diodes Schottky barrier PBYR325CTD series

MECHANICAL DATA



MOUNTING INSTRUCTIONS



Notes

- Observe the general handling precautions for electrostatic-discharge sensitive devices (ESDs) to prevent damage to MOS gate oxide.
 Epoxy meets UL94 V0 at 1/8".

Philips Semiconductors Product specification

Rectifier	diodes
Schottky	barrier

PBYR325CTD series

DEFINITIONS

Data sheet status				
Objective specification	This data sheet contains target or goal specifications for product development.			
Preliminary specification This data sheet contains preliminary data; supplementary data may be published late				
Product specification This data sheet contains final product specifications.				
Limiting values				

Limiting values

Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

Application information

Where application information is given, it is advisory and does not form part of the specification.

© Philips Electronics N.V. 1998

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, it is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent or other industrial or intellectual property rights.

LIFE SUPPORT APPLICATIONS

These products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Philips customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Philips for any damages resulting from such improper use or sale.